

## FORM PTO-1449 (MODIFIED)

LIST OF PUBLICATIONS FOR  
APPLICANT'S INFORMATION  
DISCLOSURE STATEMENT

Applicant(s): Allen et al.  
Docket No.: YOR920030175US1  
Serial No.: 10/661,041  
Filing Date: September 12, 2003  
Group: 2811

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS/SUBCLASS	FILING DATE IF APPROPRIATE
<u>Ch</u>	5,753,418	05/19/98	Tsai et al.	430/313	
<u>Ch</u>	6,009,888	01/04/00	Ye et al.	134/1.3	
<u>Ch</u>	6,316,167	11/13/01	Angelopoulos et al.	430/313	
<u>Ch</u>	6,387,798	05/14/02	Loke et al.	438/623	
<u>Ch</u>	6,514,867	02/04/03	Hui et al.	438/713	

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	COUNTRY	CLASS/SUBCLASS	TRANSLATION YES NO
<u>Ch</u>	EP 0 236 220 A1	13/04/88	Europe		

## OTHER DOCUMENTS

EXAMINER INITIAL	REF NO.	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
<u>Ch</u>		Celii et al., "Process Characterization for Tapered Contact Etch," J. Vac. Sci. Technol. B 19(5), American Vacuum Society, Pgs. 1845-1851 (Sept/Oct 2001).
<u>Ch</u>		Mahorowala et al., "Tunable Anti-Reflective Coatings with Built-In Hard Mask Properties Facilitating Thin Resist Processing," Proceedings of the SPIE, Vol. 4343, Pgs. 306-316 (2001).

Examiner

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EXAMINER INITIAL	REF. NO.	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
<u>ca</u>		Chun et al., "Contact Hole Size Reducing Methods by Using Water-Soluble Organic Over-Coating Material (WASOOM) as a Barrier Layer Toward 0.15 um Contact Hole; Resist Flow Technique I," Proc. SPIE, Vol. 3999, pgs. 620-626 (2000).
<u>ca</u>		Chung et al., "A Novel Resist Material for sub-100 nm Contact Hole Pattern," Proc. SPIE, Vol. 3999, pgs. 305-312 (2000).
<u>ca</u>		DellaGuardia et al., "193 Lithography and RELACS™ Processing for BBOL Lithography," Proc. SPIE, Vol. 4346, pgs. 1029-1040 (2001).
<u>ca</u>		Lucas et al., "193 nm Contact Photoresist Reflow Feasibility Study," Proc. SPIE, Vol. 4345, pgs. 725-736 (2001).
<u>ca</u>		Satou et al., "Sub-0.10 μm Hole Fabrication Using Bilayer Silylation Process for 193 nm Lithography," Jpn. J. Appl. Phys. 1, Vol. 38, Part 1, No. 12B, pgs 7008-7012 (December 1999).

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